

# Simon Perraud

## List of Publications by Year in descending order

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32  
papers

534  
citations

687363

13  
h-index

642732

23  
g-index

33  
all docs

33  
docs citations

33  
times ranked

840  
citing authors

#	ARTICLE	IF	CITATIONS
1	CIGS solar cells on ultra-thin glass substrates: Determination of mechanical properties by nanoindentation and application to bending-induced strain calculation. <i>Solar Energy Materials and Solar Cells</i> , 2017, 166, 254-261.	6.2	23
2	Influence of coevaporation process on CIGS solar cells with reduced absorber thickness and current enhancement with periodically textured glass substrates. <i>Thin Solid Films</i> , 2017, 621, 188-194.	1.8	8
3	Looped energy harvester for human motion. <i>Smart Materials and Structures</i> , 2017, 26, 105035.	3.5	6
4	Indium tin oxide-silicon nanocrystal nanocomposite grown by aerosol assisted chemical vapour deposition. <i>Journal of Sol-Gel Science and Technology</i> , 2015, 73, 666-672.	2.4	3
5	CIGS solar cells on flexible ultra-thin glass substrates: Characterization and bending test. <i>Thin Solid Films</i> , 2015, 592, 99-104.	1.8	35
6	Minority Carrier Lifetime Measurement in Nanowire Based Solar Cells by a Reverse Recovery Transient Method. <i>Energy Procedia</i> , 2014, 60, 181-190.	1.8	0
7	Sodium-doped Mo back contacts for Cu(In,Ga)Se <sub>2</sub> solar cells on Ti foils: Growth, morphology, and sodium diffusion. <i>Journal of Renewable and Sustainable Energy</i> , 2014, 6, 011405.	2.0	8
8	Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> thin films for photovoltaic applications: Influence of the precursor stacking order on the selenization process. <i>Journal of Alloys and Compounds</i> , 2014, 588, 310-315.	5.5	19
9	Analysis of photovoltaic properties of Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> -based solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2014, 126, 135-142.	6.2	17
10	Structural analysis of the interface of silicon nanocrystals embedded in a Si <sub>3</sub> N <sub>4</sub> matrix. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 255302.	2.8	9
11	Experimental evidence of light soaking effect in Cd-free Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> -based solar cells. <i>Thin Solid Films</i> , 2014, 564, 375-378.	1.8	29
12	Comparison of optical properties of Si and ZnO/CdTe core/shell nanowire arrays. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2013, 178, 665-669.	3.5	19
13	Characteristics of molybdenum bilayer back contacts for Cu(In,Ga)Se <sub>2</sub> solar cells on Ti foils. <i>Thin Solid Films</i> , 2013, 548, 608-616.	1.8	18
14	Silicon nanocrystals: Novel synthesis routes for photovoltaic applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 649-657.	1.8	8
15	Influence of sodium-containing substrates on Kesterite CZTSSe thin films based solar cells. <i>Materials Research Society Symposia Proceedings</i> , 2013, 1538, 103-106.	0.1	10
16	Silicon nanocrystals on amorphous silicon carbide alloy thin films: Control of film properties and nanocrystals growth. <i>Thin Solid Films</i> , 2012, 522, 136-144.	1.8	7
17	Aluminum catalyzed growth of silicon nanowires: Al atom location and the influence of silicon precursor pressure on the morphology. <i>Journal of Crystal Growth</i> , 2012, 341, 12-18.	1.5	25
18	Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> based solar cell produced by selenization of vacuum deposited precursors. <i>Solar Energy Materials and Solar Cells</i> , 2012, 101, 11-14.	6.2	78

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19	The Effects of Using ALD-Grown ZnO Buffer Layers on the Properties of Indium Tin Oxide Grown by Chemical Solution Deposition. <i>Journal of Nanoscience and Nanotechnology</i> , 2011, 11, 8354-8357.	0.9	0
20	Conductive-probe atomic force microscopy characterization of silicon nanowire. <i>Nanoscale Research Letters</i> , 2011, 6, 110.	5.7	37
21	Al catalyzed growth of silicon nanowires and subsequent in situ dry etching of the catalyst for photovoltaic application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 2676-2680.	1.8	9
22	Study of CVD nanowire high-k metal interface quality for interconnect level MOS devices. <i>Microelectronic Engineering</i> , 2011, 88, 1228-1231.	2.4	0
23	Patterned growth of high aspect ratio silicon wire arrays at moderate temperature. <i>Journal of Crystal Growth</i> , 2011, 321, 151-156.	1.5	10
24	Full process for integrating silicon nanowire arrays into solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2009, 93, 1568-1571.	6.2	80
25	Bound states induced by a single donor in a semiconductor quantum well: A scanning tunneling spectroscopy study. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1418-1420.	2.7	0
26	Spatial imaging of valence band electronic structures in a GaSb/InAs quantum well. <i>Applied Surface Science</i> , 2008, 254, 7889-7892.	6.1	1
27	Direct Measurement of the Binding Energy and Bohr Radius of a Single Hydrogenic Defect in a Semiconductor Quantum Well. <i>Physical Review Letters</i> , 2008, 100, 056806.	7.8	16
28	Imaging the percolation of localized states in a multisubband two-dimensional electronic system subject to a disorder potential. <i>Physical Review B</i> , 2007, 76, .	3.2	7
29	Imaging of Interference between Incident and Reflected Electron Waves at an InAs/GaSb Heterointerface by Low-Temperature Scanning Tunneling Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 2618-2621.	1.5	4
30	Spatial Imaging of Two-Dimensional Electronic States in Semiconductor Quantum Wells. <i>Physical Review Letters</i> , 2007, 98, 136802.	7.8	42
31	Dramatic dependence of the Fermi level pinning strength on crystal orientation at clean surfaces of n-type In <sub>0.53</sub> Ga <sub>0.47</sub> As grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007, 301-302, 148-151.	1.5	1
32	Unpinning of the Fermi level at (111)A clean surfaces of epitaxially grown n-type In <sub>0.53</sub> Ga <sub>0.47</sub> As. <i>Applied Physics Letters</i> , 2006, 89, 192110.	3.3	5